

isc Silicon NPN Power Transistor

2SC6011/A

DESCRIPTION

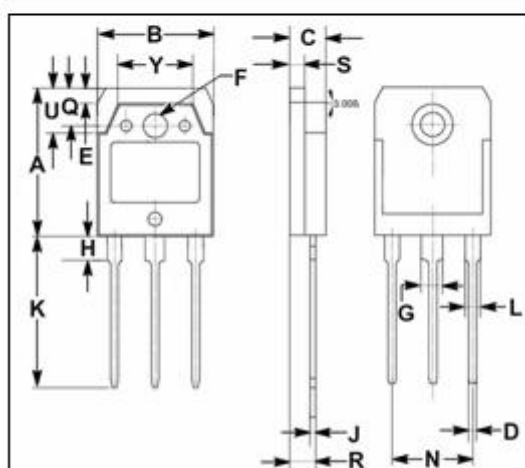
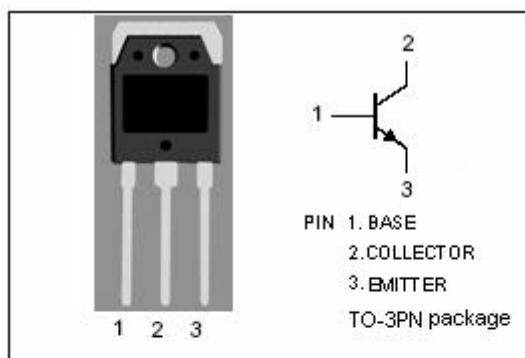
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 200V(\text{Min})-2SC6011$
= $200V(\text{Min})-2SC6011A$
- Good Linearity of h_{FE}
- Complement to Type 2SA2151/A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	2SC6011	200
		2SC6011A	230
V_{CEO}	Collector-Emitter Voltage	2SC6011	200
		2SC6011A	230
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	160	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

isc Silicon NPN Power Transistor**2SC6011/A****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	2SC6011	I _C = 50mA ; I _B = 0	200			V
		2SC6011A		230			
V _{CE(sat)}	Collector-Emitter Saturation Voltage		I _C = 5A; I _B = 0.5A			0.5	V
I _{CBO}	Collector Cutoff Current	2SC6011	V _{CB} = 200V ; I _E = 0			10	μ A
		2SC6011A	V _{CB} = 230V ; I _E = 0				
I _{EBO}	Emitter Cutoff Current		V _{EB} = 6V; I _C = 0			10	μ A
h _{FE}	DC Current Gain		I _C = 3A ; V _{CE} = 4V	50		180	
C _{OB}	Output Capacitance		I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz		270		pF
f _T	Current-Gain—Bandwidth Product		I _E = -0.5A ; V _{CE} = 12V		20		MHz

◆ **h_{FE} Classifications**

O	P	Y
50-100	70-140	90-180